1-Gbps to 4.25-Gbps Rate-Selectable Limiting Amplifier

FEATURES

- **Multirate Operation from 1 Gbps up to 4.25 Gbps**
- **Loss-of-Signal Detection (LOS)**
- **Two-Wire Digital Interface**
- **Digitally Selectable LOS Threshold**
- **Digitally Selectable Bandwidth**
- **Digitally Selectable Output Voltage**
- **Low Power Consumption**
- **Input Offset Cancellation**

- **CML Data Outputs With On-Chip, 50-Ω Back-Termination to V_{CC}**
- **Single 3.3-V Supply**
- **Surface-Mount, Small-Footprint, 4-mm $\times$ 4-mm, 16-Terminal QFN Package**

APPLICATIONS

- **Multirate SONET/SDH Transmission Systems**
- **4.25-Gbps, 2.125-Gbps, and 1.0625-Gbps Fibre-Channel Receivers**
- **Gigabit Ethernet Receivers**

DESCRIPTION

The ONET4291PA is a versatile, high-speed, rate-selectable limiting amplifier for multiple fiber-optic applications with data rates up to 4.25 Gbps.

The device provides a two-wire interface, which allows digital bandwidth selection, digital output amplitude selection, and digital loss of signal threshold adjust.

This device provides a gain of about 43 dB, which ensures a fully differential output swing for input signals as low as 5 mV$_{p-p}$.

The ONET4291PA provides loss-of-signal detection with either digital or analog threshold adjust.

The part is available in a small-footprint, 4-mm $\times$ 4-mm, 16-terminal QFN package. It requires a single 3.3-V supply.

This power-efficient, rate-selectable limiting amplifier is characterized for operation from –40°C to 85°C ambient temperature.
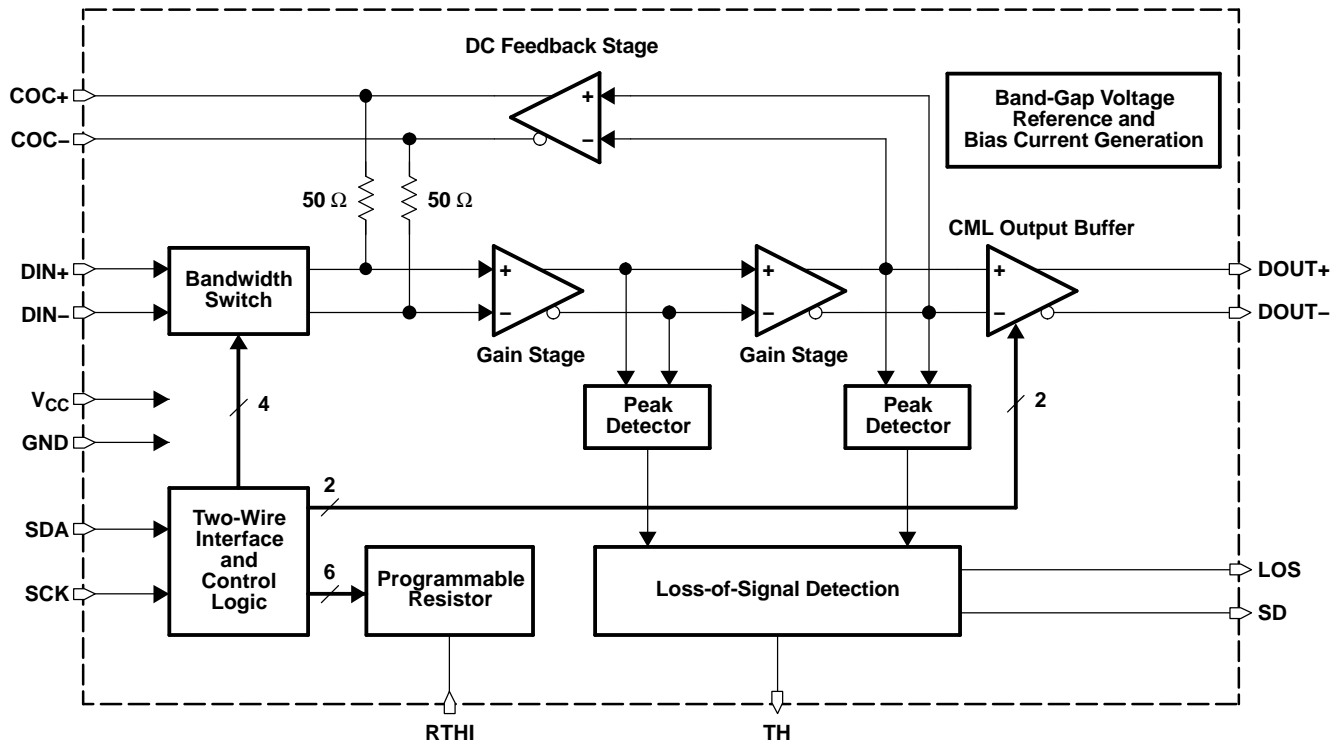
BLOCK DIAGRAM

A simplified block diagram of the ONET4291PA is shown in Figure 1.

This compact, 3.3-V, low-power, 1-Gbps to 4.25-Gbps rate-selectable limiting amplifier consists of a high-speed data path with offset cancellation block (dc feedback), a loss-of-signal detection block using two peak detectors, a programmable resistor, a two-wire interface and control-logic block, and a band-gap voltage reference and bias-current generation block.

Figure 1. Simplified Block Diagram of the ONET4291PA

HIGH-SPEED DATA PATH

The high-speed data signal is applied to the data path by means of the input signal terminals DIN+ and DIN–. The data path consists of a digitally controllable bandwidth switch followed by two 50-Ω on-chip line termination resistors; two gain stages, which provide a typical gain of about 37 dB; and a CML output stage, which provides another 6-dB gain. The amplified data-output signal is available at the output terminals DOUT+ and DOUT–, which feature on-chip 2×50-Ω back-termination to V_{CC}.

A dc feedback stage compensates for internal offset voltages and thus ensures proper operation even for small input data signals. This stage is driven by the output signal of the second gain stage. The signal is low-pass filtered, amplified, and fed back to the input of the first gain stage via the on-chip 50-Ω termination resistors. The required low-frequency cutoff is determined by an external 0.1-μF capacitor, which must be differentially connected to the COC+ and COC– terminals.

LOSS-OF-SIGNAL DETECTION AND PROGRAMMABLE RESISTOR

The peak values of the output signals of the first and second gain stages are monitored by two peak detectors. The peak values are compared to a predefined loss-of-signal threshold voltage inside the loss-of-signal detection block. As a result of the comparison, the loss-of-signal detection block generates the SD signal, which indicates a sufficient input-signal amplitude, or the LOS signal, which indicates that the input signal amplitude is below the defined threshold level.

The threshold voltage can be set within a certain range by means of an external resistor connected between the TH terminal and ground (GND). Alternatively, shorting the TH and RTHI terminals causes an internal, digitally selectable resistor to be used for threshold adjustment. The resistor value is selectable using the two-wire interface.

The principle of the digitally selectable resistor is shown in Figure 2. The complete resistor between the RTHI terminal and GND consists of seven series-connected resistors.

Six of the resistors have binary-weighted resistance values, and each can be shunted individually by means of a parallel-connected MOS transistor.

The seventh resistor defines the minimum remaining resistance in case all six MOS devices are conductive.

With the resistor values shown in Figure 2, the minimum selectable resistance is 8 kΩ, the maximum resistance is 86.75 kΩ, and the resolution is 1.25 kΩ/step.
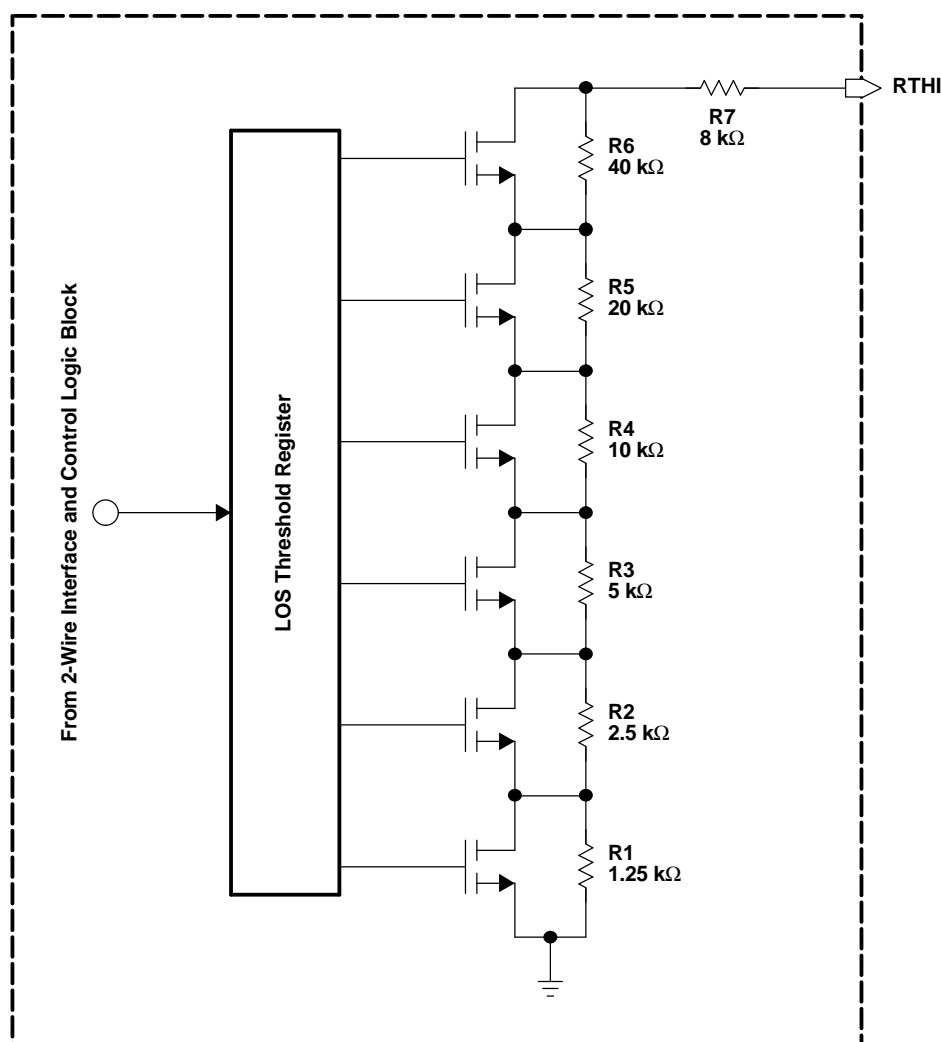
S0098-01

Figure 2. Digitally Controllable On-Chip Resistor

TWO-WIRE INTERFACE AND CONTROL LOGIC

The ONET4291PA uses a two-wire serial interface for digital control of the amplifier bandwidth, output amplitude, and LOS threshold. A simplified block diagram of this interface is given in Figure 3.

SDA and SCK are inputs for the serial data and the serial clock, respectively, and can be driven by a microprocessor. Both inputs have 100-kΩ pullup resistors to V_{CC}. For driving these inputs, an open-drain output is recommended.

A write cycle consists of a START command, 3 address bits with MSB first, 8 data bits with MSB first, and a STOP command. In idle mode, both the SDA and SCK lines are at a high level.

A START command is initiated by a falling edge on SDA with SCK at a high level.

Bits are clocked into an 11-bit-wide shift register while the SCK level is high.

A STOP command is detected on the rising edge of SDA after SCK has changed from a low level to a high level.

At the time of detection of a STOP command, the 8 data bits from the shift register are copied to a selected 8-bit register. Register selection occurs according to the 3 address bits in the shift register, which are decoded to 8 independent select signals using a 3-to-8 decoder block.

In the ONET4291PA, only addresses 4 (100b) and 5 (101b) are used.
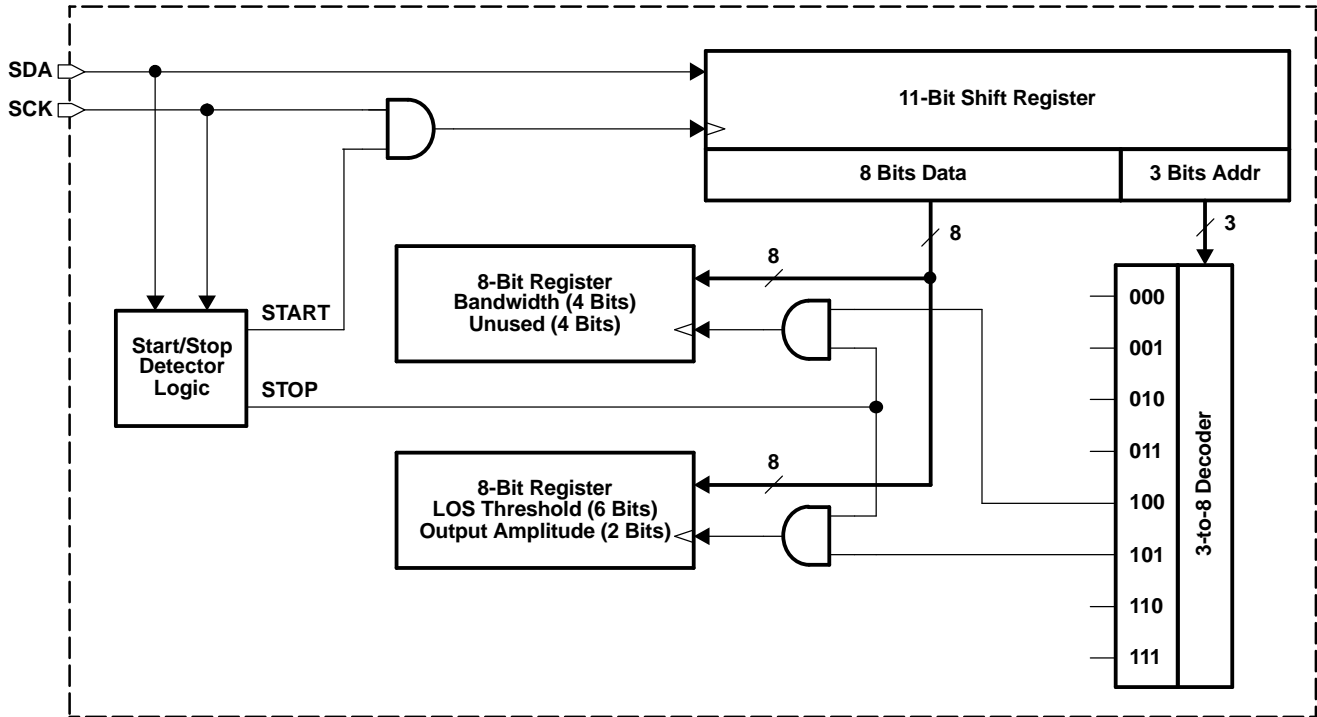
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Figure 3. Simplified Two-Wire Interface Block Diagram

The timing definition for the serial data signal SDA and the serial clock signal SCK is shown in Figure 4.

Figure 4. Two-Wire Interface Timing Diagram
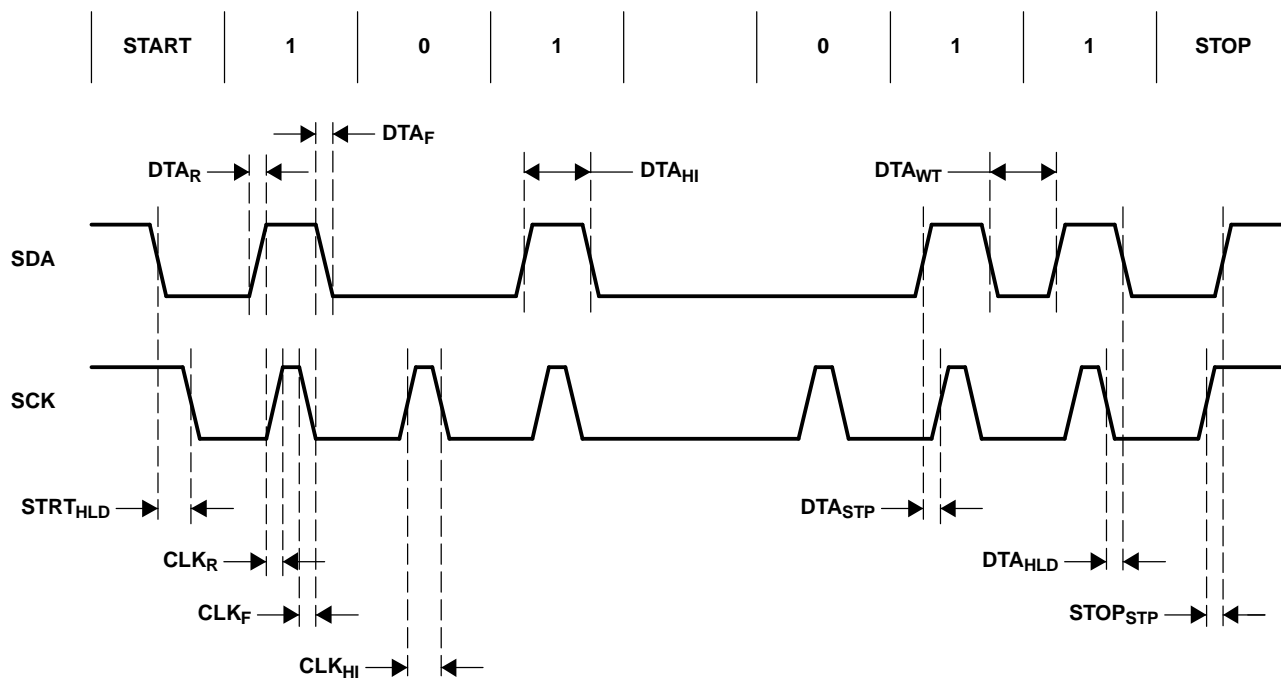
PARAMETER		DESCRIPTION	MIN	MAX	UNIT
$STRT_{HLD}$	START hold time	Time required from data falling edge to clock falling edge at START	10		ns
CLK_R, DTA_R	Clock and data rise time	Clock and data rise time		10	ns
CLK_F, DTA_F	Clock and data fall time	Clock and data fall time		10	ns
CLK_{HI}	Clock high time	Minimum clock high period	50		ns
DTA_{HI}	Data high time	Minimum data high period	100		ns
DTA_{STP}	Data setup time	Minimum time from data rising edge to clock rising edge	10		ns
DTA_{WT}	Data wait time	Minimum time from data falling edge to data rising edge	50		ns
DTA_{HLD}	Data hold time	Minimum time from clock falling edge to data falling edge	10		ns
$STOP_{STP}$	STOP setup time	Minimum time from clock rising edge to data rising edge at STOP	10		ns

The register mapping for register addresses 4 (100b) and 5 (101b) is shown in Table 1 and Table 2, respectively.

Table 1. Register 4 (100b) Mapping

BIT 7	BIT 6	BIT 5	BIT 4	BIT 3	BIT 2	BIT 1	BIT 0
BW3	BW2	BW1	BW0	–	–	–	–

Table 2. Register 5 (101b) Mapping

BIT 7	BIT 6	BIT 5	BIT 4	BIT 3	BIT 2	BIT 1	BIT 0
A1	A0	R5	R4	R3	R2	R1	R0

Table 3 through Table 5 describe circuit functionality based on the register settings.

TEXAS
INSTRUMENTS
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Table 3. Bandwidth Selection

BW3	BW2	BW1	BW0	TYP	UNIT
0	0	0	0	4.39	GHz
0	0	0	1	3.91	GHz
0	0	1	0	3.47	GHz
0	0	1	1	3.03	GHz
0	1	0	0	2.81	GHz
0	1	0	1	2.31	GHz
0	1	1	0	1.82	GHz
0	1	1	1	1.60	GHz
1	0	0	0	1.55	GHz
1	0	0	1	1.33	GHz
1	0	1	0	1.11	GHz
1	0	1	1	1.03	GHz
1	1	0	0	0.86	GHz
1	1	0	1	0.82	GHz
1	1	1	0	0.76	GHz
1	1	1	1	0.73	GHz

Table 4. Output Amplitude Selection

A1	A0	TYP	UNIT
0	0	400	mV_{p-p}
0	1	600	mV_{p-p}
1	0	800	mV_{p-p}
1	1	1000	mV_{p-p}

Table 5. LOS-Threshold Digitally Controlled Resistor Selection

R5	R4	R3	R2	R1	R0	TYP	UNIT
0	0	0	0	0	0	86.75	$k\Omega$
0	0	0	0	0	1	85.5	$k\Omega$
0	0	0	0	1	0	84.25	$k\Omega$
0	0	0	0	1	1	83	$k\Omega$
0	0	0	1	0	0	81.75	$k\Omega$
0	0	0	1	0	1	80.5	$k\Omega$
0	0	0	1	1	0	79.25	$k\Omega$
0	0	0	1	1	1	78	$k\Omega$
0	0	1	0	0	0	76.75	$k\Omega$
0	0	1	0	0	1	75.5	$k\Omega$
0	0	1	0	1	0	74.25	$k\Omega$
0	0	1	0	1	1	73	$k\Omega$
0	0	1	1	0	0	71.75	$k\Omega$
0	0	1	1	0	1	70.5	$k\Omega$
0	0	1	1	1	0	69.25	$k\Omega$
0	0	1	1	1	1	68	$k\Omega$
0	1	0	0	0	0	66.75	$k\Omega$
0	1	0	0	0	1	65.5	$k\Omega$
0	1	0	0	1	0	64.25	$k\Omega$
0	1	0	0	1	1	63	$k\Omega$
0	1	0	1	0	0	61.75	$k\Omega$

Table 5. LOS-Threshold Digitally Controlled Resistor Selection (continued)

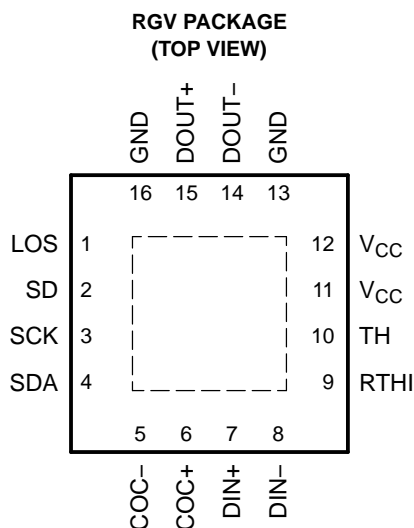| R5	R4	R3	R2	R1	R0	TYP	UNIT
0	1	0	1	0	1	60.5	kΩ
0	1	0	1	1	0	59.25	kΩ
0	1	0	1	1	1	58	kΩ
0	1	1	0	0	0	56.75	kΩ
0	1	1	0	0	1	55.5	kΩ
0	1	1	0	1	0	54.25	kΩ
0	1	1	0	1	1	53	kΩ
0	1	1	1	0	0	51.75	kΩ
0	1	1	1	0	1	50.5	kΩ
0	1	1	1	1	0	49.25	kΩ
0	1	1	1	1	1	48	kΩ
1	0	0	0	0	0	46.75	kΩ
1	0	0	0	0	1	45.5	kΩ
1	0	0	0	1	0	44.25	kΩ
1	0	0	0	1	1	43	kΩ
1	0	0	1	0	0	41.75	kΩ
1	0	0	1	0	1	40.5	kΩ
1	0	0	1	1	0	39.25	kΩ
1	0	0	1	1	1	38	kΩ
1	0	1	0	0	0	36.75	kΩ
1	0	1	0	0	1	35.5	kΩ
1	0	1	0	1	0	34.25	kΩ
1	0	1	0	1	1	33	kΩ
1	0	1	1	0	0	31.75	kΩ
1	0	1	1	0	1	30.5	kΩ
1	0	1	1	1	0	29.25	kΩ
1	0	1	1	1	1	28	kΩ
1	1	0	0	0	0	26.75	kΩ
1	1	0	0	0	1	25.5	kΩ
1	1	0	0	1	0	24.25	kΩ
1	1	0	0	1	1	23	kΩ
1	1	0	1	0	0	21.75	kΩ
1	1	0	1	0	1	20.5	kΩ
1	1	0	1	1	0	19.25	kΩ
1	1	0	1	1	1	18	kΩ
1	1	1	0	0	0	16.75	kΩ
1	1	1	0	0	1	15.5	kΩ
1	1	1	0	1	0	14.25	kΩ
1	1	1	0	1	1	13	kΩ
1	1	1	1	0	0	11.75	kΩ
1	1	1	1	0	1	10.5	kΩ
1	1	1	1	1	0	9.25	kΩ
1	1	1	1	1	1	8	kΩ

BAND-GAP VOLTAGE AND BIAS GENERATION

The ONET4291PA limiting amplifier is supplied by a single, 3.3-V supply voltage connected to the V_{CC} terminals. This voltage is referred to GND.

On-chip band-gap voltage circuitry generates a reference voltage, independent of supply voltage, from which all other internally required voltages and bias currents are derived.

TERMINAL ASSIGNMENTS

For the ONET4291PA, a small-footprint 4-mm × 4-mm, 16-terminal QFN package is used, with a terminal pitch of 0,65 mm.

RGV PACKAGE
(TOP VIEW)

P0030-01

TERMINAL DESCRIPTION

TERMINAL		TYPE	DESCRIPTION
NAME	NO.		
COC+	6	Analog	Offset cancellation filter capacitor plus terminal. An external 0.1-μF filter capacitor must be connected between this terminal and COC− (terminal 5).
COC−	5	Analog	Offset cancellation filter capacitor minus terminal. An external 0.1-μF filter capacitor must be connected between this terminal and COC+ (terminal 6).
DIN+	7	Analog input	Non-inverted data input. On-chip 50-Ω terminated to COC+. Differentially 100-Ω terminated to DIN−.
DIN−	8	Analog input	Inverted data input. On-chip 50-Ω terminated to COC−. Differentially 100-Ω terminated to DIN+.
DOUT+	15	CML output	Non-inverted data output. On-chip 50-Ω back-terminated to V_{CC}.
DOUT−	14	CML output	Inverted data output. On-chip 50-Ω back-terminated to V_{CC}.
GND	13, 16, EP	Supply	Circuit ground. Exposed die pad (EP) must be grounded.
LOS	1	Open-drain MOS	High level indicates that the input signal amplitude is below the programmed threshold level. Open-drain output. Requires an external 10-kΩ pullup resistor to V_{CC} for proper operation.
RTHI	9	Analog	Digitally controlled internal resistor to ground, which can be used for LOS threshold adjustment. A 6-bit-wide control register can be set via the two-wire interface.
SCK	3	CMOS input	Two-wire interface serial clock. Includes a 100-kΩ pullup resistor to V_{CC}.
SD	2	CMOS output	High level indicates that sufficient input signal amplitude is applied to the device. Low level indicates that the input signal amplitude is below the programmed threshold level.
SDA	4	CMOS input	Two-wire interface serial data input. Includes a 100-kΩ pullup resistor to V_{CC}.
TH	10	Analog input	LOS threshold adjustment with resistor to GND. For use of the internal digitally controlled resistor, connect TH with RTHI (terminal 9).
V_{CC}	11, 12	Supply	3.3-V, +10%/−12% supply voltage

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) [1]

V_{CC}	Supply voltage [2]	−0.3 V to 4 V
V_{DIN+}, $V_{DIN−}$	Voltage at DIN+, DIN−[2]	0.5 V to 4 V
V_{LOS}, V_{SD}, V_{SCK}, V_{SDA}, V_{COC+}, $V_{COC−}$, V_{RTHI}, V_{TH}, V_{DOUT+}, $V_{DOUT−}$	Voltage at LOS, SD, SCK, SDA, COC+, COC−, RTHI, TH, DOUT+, DOUT−[2]	−0.3 V to 4 V
$V_{DIN,DIFF}$	Differential voltage between DIN+ and DIN−	±1.25 V
I_{LOS}	Current into LOS	10 mA
I_{DIN+}, $I_{DIN−}$, I_{DOUT+}, $I_{DOUT−}$	Continuous current at inputs and outputs	20 mA
ESD	ESD rating at all terminals (HBM)	4 kV
$T_{J,max}$	Maximum junction temperature	125°C
T_{stg}	Storage temperature range	−65°C to 85°C
T_A	Characterized free-air operating temperature range	−40°C to 85°C
T_{LEAD}	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values are with respect to network ground terminal.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}, V_{CCO}	Supply voltage	2.9	3.3	3.6	V
T_A	Operating free-air temperature	−40		85	°C
	CMOS input high voltage	2			V
	CMOS input low voltage			0.8	V

DC ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted). Typical values are at V_{CC} = 3.3 V and T_A = 25°C.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{CC}, V_{CCO}	Supply voltage		2.9	3.3	3.6	V
I_{VCC}	Supply current [1]	V_{OD} = 1000 mV$_{p-p}$, maximum bandwidth selected	35	50	64	mA
		V_{OD} = 800 mV$_{p-p}$, maximum bandwidth selected	32	46	59	
		V_{OD} = 600 mV$_{p-p}$, maximum bandwidth selected	28	41	53	
		V_{OD} = 400 mV$_{p-p}$, maximum bandwidth selected	24	36	48	
R_{IN}, R_{OUT}	Data input/output resistance	Single-ended		50		Ω
	CMOS output high voltage	I_{SINK} = 1 mA	2.3			V
	CMOS output low voltage	I_{SOURCE} = 1 mA			0.5	V
	LOS low voltage	I_{SOURCE} = 1.5 mA			0.5	V
	Optimum LOS threshold resistor		12		62	kΩ

(1) Use of the bandwidth select switch increases current consumption. The MSB bandwidth-select bit, BW3, typically consumes 5 mA, BW2 2.6 mA, BW1 1.3 mA, and BW0 0.7 mA.

AC ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted). Typical operating condition is at V_{CC} = 3.3 V and T_A = 25°C.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_{3dB-H}	High-frequency −3-dB bandwidth	Maximum bandwidth selected (BW3 = BW2 = BW1 = BW0 = 0)	3.5	4.5	6	GHz
		Minimum bandwidth selected (BW3 = BW2 = BW1 = BW0 = 1)	0.7			
f_{3dB-L}	Low-frequency −3-dB bandwidth	C_{OC} = 0.1 µF		23	50	kHz
	Data rate	Maximum bandwidth selected (BW3 = BW2 = BW1 = BW0 = 0)	4.25			Gbps
$v_{IN,MIN}$	Data input sensitivity	K28.5 at 4.25 Gbps, BER < 10^{-12} (noise limited)		1.9	2.7	mV_{p-p}
		V_{OD-min} ≥ 0.95 * V_{OD} (at V_{IN} = 25 mV_{p-p}) (gain limited)		8	14	
A	Small-signal gain		38	43	46	dB
	Small-signal gain vs temperature				2.5	dB
	Small-signal gain vs supply voltage V_{CC}				1	dB
$v_{IN,MAX}$	Data input overload		2000			mV_{p-p}
DJ	Deterministic jitter	v_{IN} = 5 mV_{p-p}, K28.5 at 4.25 Gbps, maximum bandwidth		10	18	ps_{p-p}
		v_{IN} = 10 mV_{p-p}, K28.5 at 4.25 Gbps, maximum bandwidth		9	17	
		v_{IN} = 25 mV_{p-p}, K28.5 at 4.25 Gbps, maximum bandwidth		8	15	
RJ	Random jitter	Input = 5 mV_{p-p}, maximum bandwidth		3		ps_{RMS}
		Input = 10 mV_{p-p}, maximum bandwidth		1.5		
V_{OD}	Differential-data output voltage	800-mV output amplitude selected (default), v_{IN} > 25 mV_{p-p}	700	850	1000	mV_{p-p}
t_R	Output rise time	20% to 80%, v_{IN} > 25 mV_{p-p}, maximum bandwidth		45	90	ps
t_F	Output fall time	20% to 80%, v_{IN} > 25 mV_{p-p}, maximum bandwidth		45	90	ps
V_{TH}	LOS assert threshold range	K28.5 pattern at 4.25 Gbps, R_{TH} = 62 kΩ		5.5		mV_{p-p}
		K28.5 pattern at 4.25 Gbps, R_{TH} = 12 kΩ		30		
	LOS threshold variation vs temperature			1		dB
	LOS threshold variation vs supply voltage V_{CC}				1.5	dB
	LOS hysteresis	K28.5 pattern at 4.25 Gbps	2		7.4	dB
T_{LOS_AST}	LOS assert time		400		1500	ns
T_{LOS_DEA}	LOS deassert time		15		80	ns

TYPICAL CHARACTERISTICS

Typical operating condition is at V_{CC} = 3.3 V and T_A = 25°C.

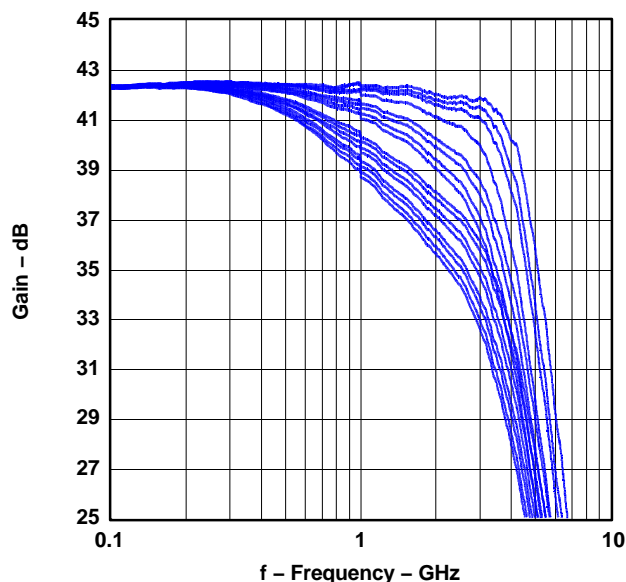**FREQUENCY RESPONSE FOR**
DIFFERENT BANDWIDTH SETTINGS

Figure 5.

BANDWIDTH
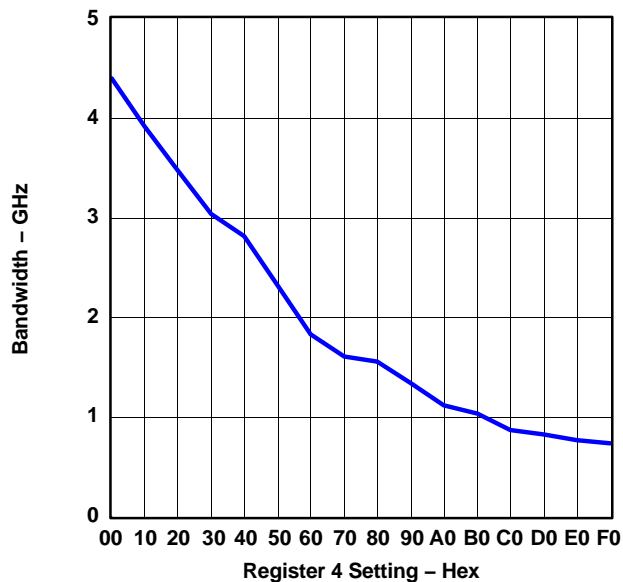**vs**
REGISTER-4 SETTING

Figure 6.

DIFFERENTIAL INPUT RETURN GAIN
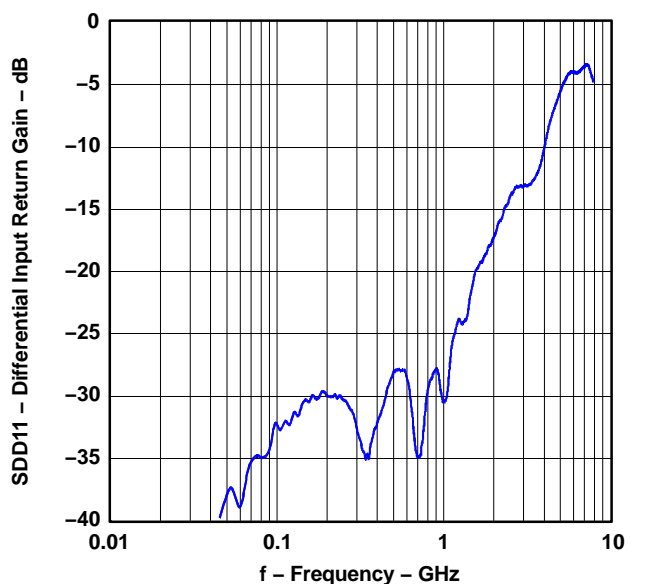**vs**
FREQUENCY (MAXIMUM BANDWIDTH)

Figure 7.

RANDOM JITTER
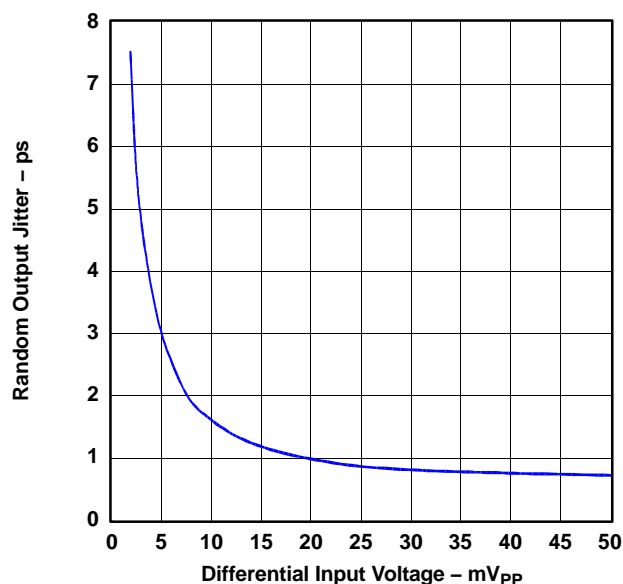**vs**
INPUT AMPLITUDE (4.25 Gbps, MAXIMUM BANDWIDTH)

Figure 8.

TYPICAL CHARACTERISTICS (continued)

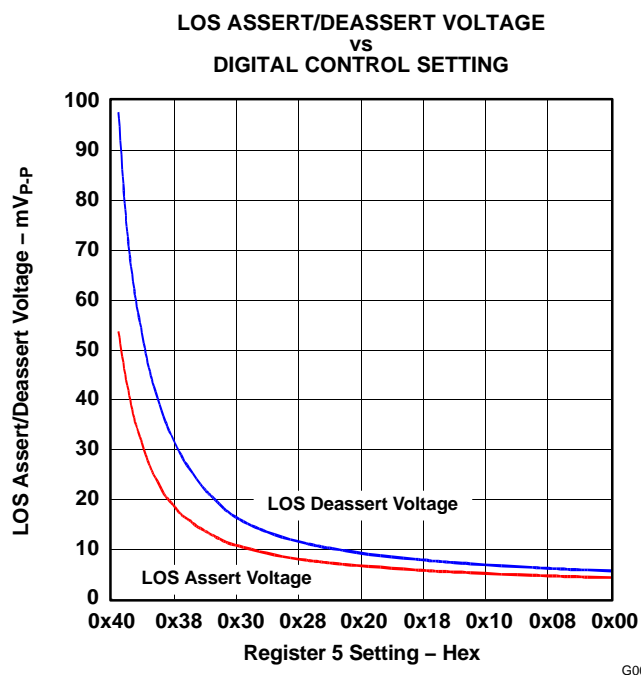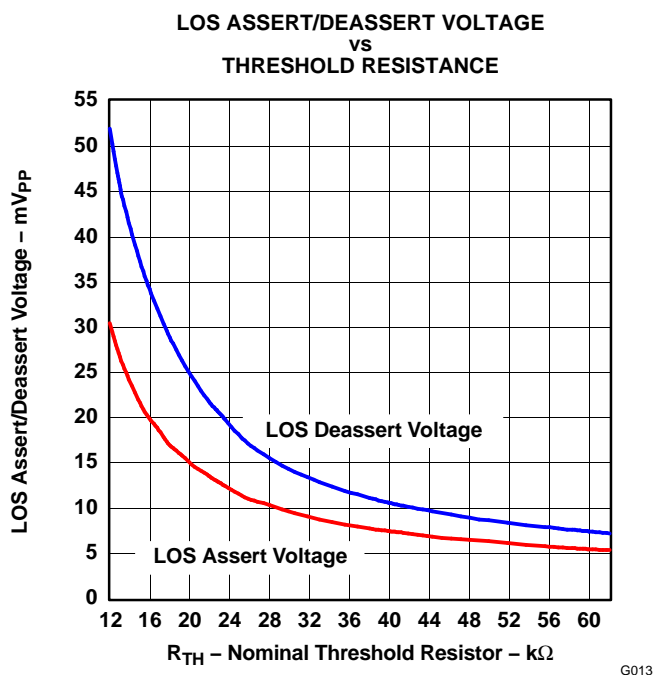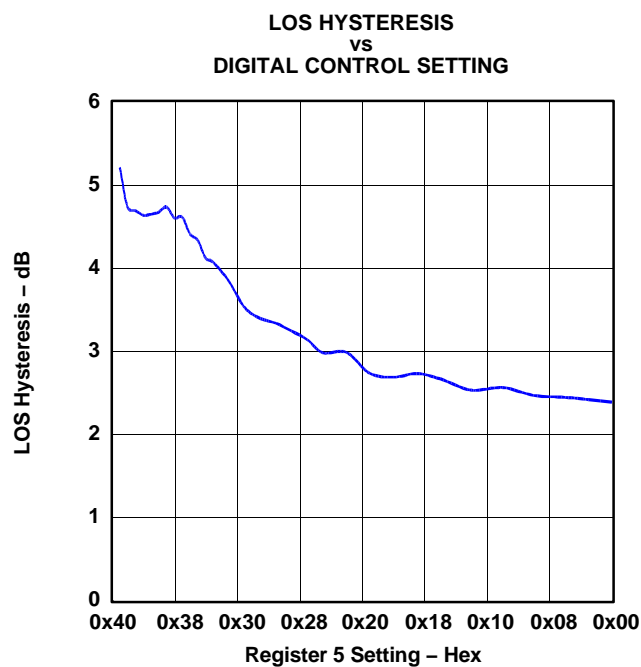Typical operating condition is at V_{CC} = 3.3 V and T_A = 25°C.

**BIT-ERROR RATIO
vs
INPUT AMPLITUDE (4.25 Gbps, MAXIMUM BANDWIDTH)**

Figure 9.

**LOS ASSERT/DEASSERT VOLTAGE
vs
DIGITAL CONTROL SETTING**

Figure 10.

**LOS ASSERT/DEASSERT VOLTAGE
vs
THRESHOLD RESISTANCE**

Figure 11.

**LOS HYSTERESIS
vs
DIGITAL CONTROL SETTING**
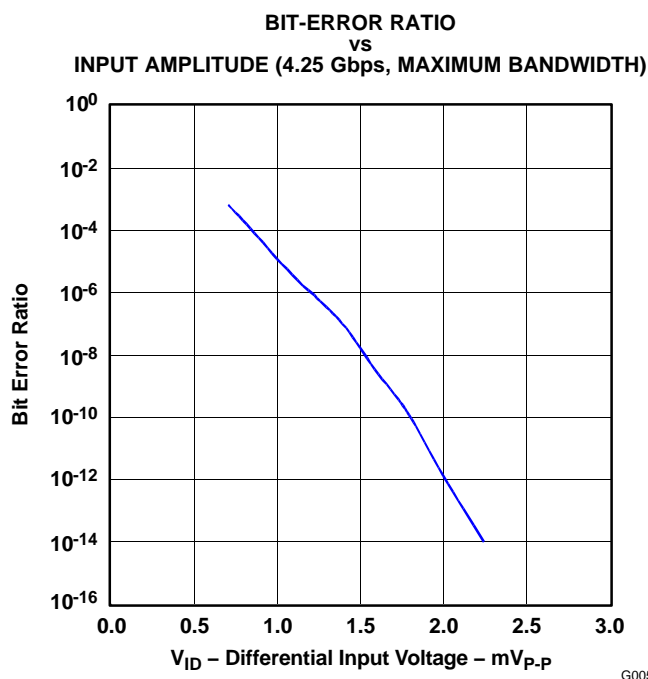
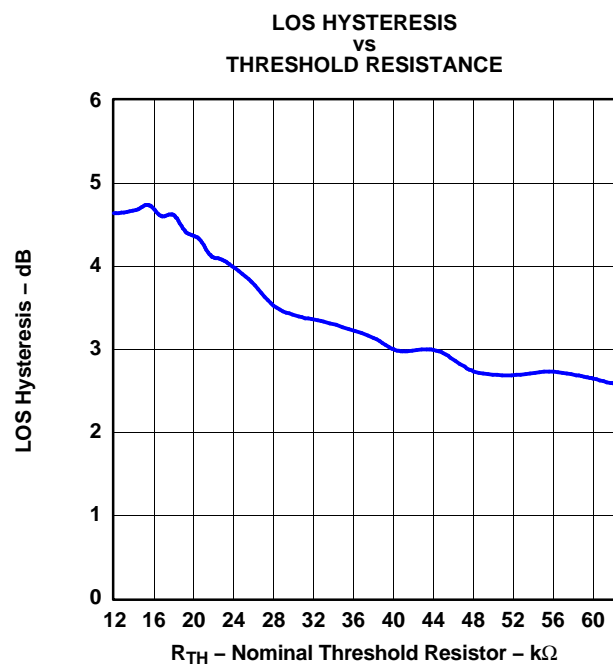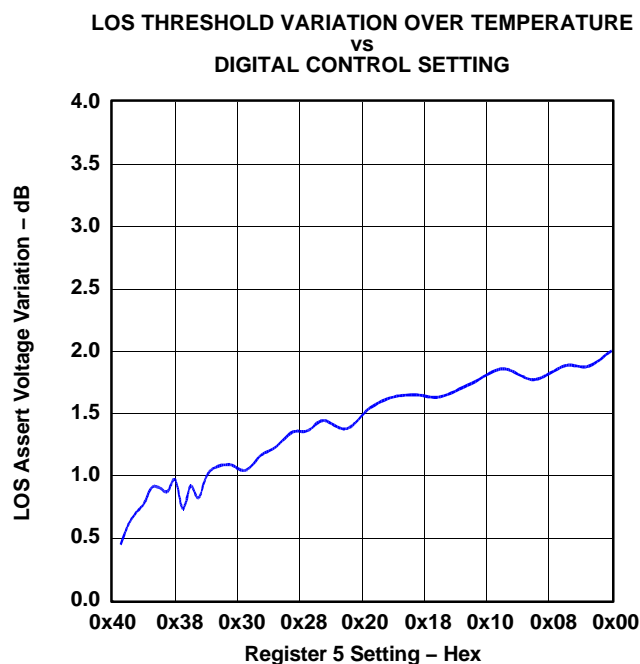Figure 12.

TYPICAL CHARACTERISTICS (continued)

Typical operating condition is at V_{CC} = 3.3 V and T_A = 25°C.

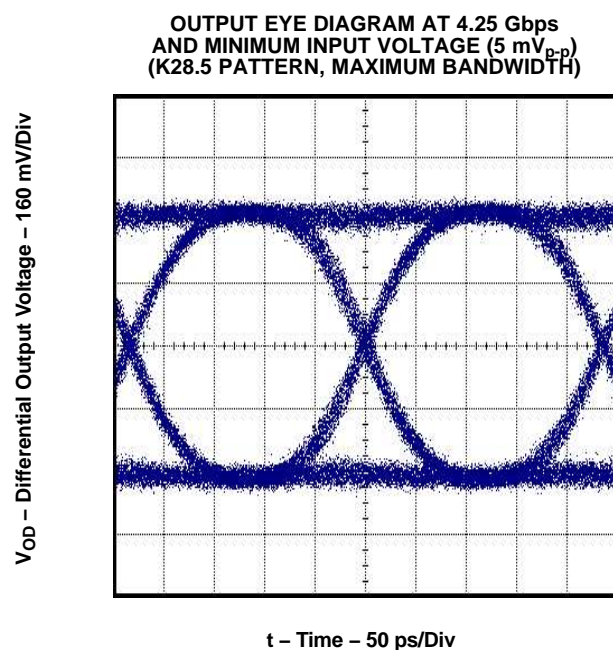**Figure 13.**

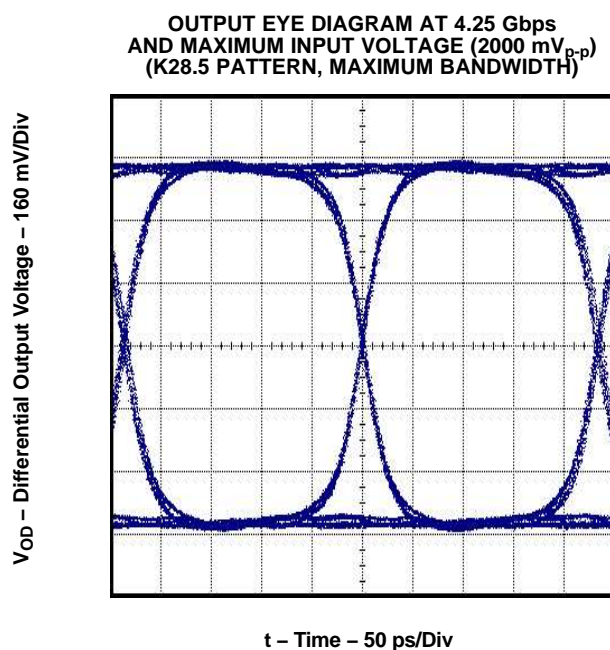**Figure 14.**

Figure 15.

Figure 16.

TYPICAL CHARACTERISTICS (continued)

Typical operating condition is at V_{CC} = 3.3 V and T_A = 25°C.

**OUTPUT EYE DIAGRAM AT 1.0625 Gbps
AND MINIMUM INPUT VOLTAGE (5 mV$_{p-p}$)
(K28.5 PATTERN, REGISTER 4 SET TO 0x70)**

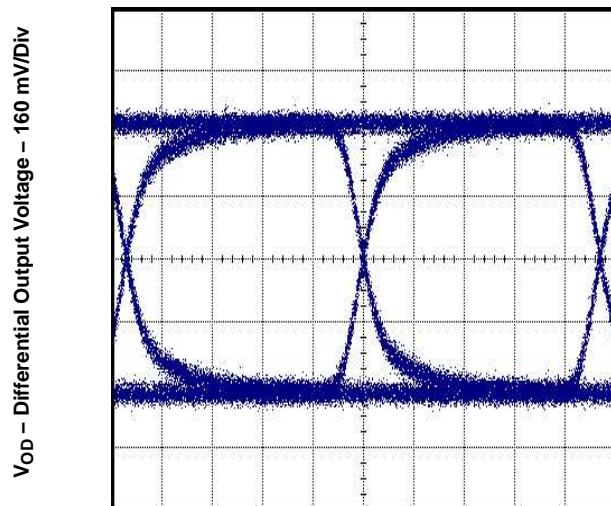V_{OD} – Differential Output Voltage – 160 mV/Div

t – Time – 200 ps/Div

G011

Figure 17.

**OUTPUT EYE DIAGRAM AT 1.0625 Gbps
AND MAXIMUM INPUT VOLTAGE (2000 mV$_{p-p}$)
(K28.5 PATTERN, REGISTER 4 SET TO 0x70)**

V_{OD} – Differential Output Voltage – 160 mV/Div
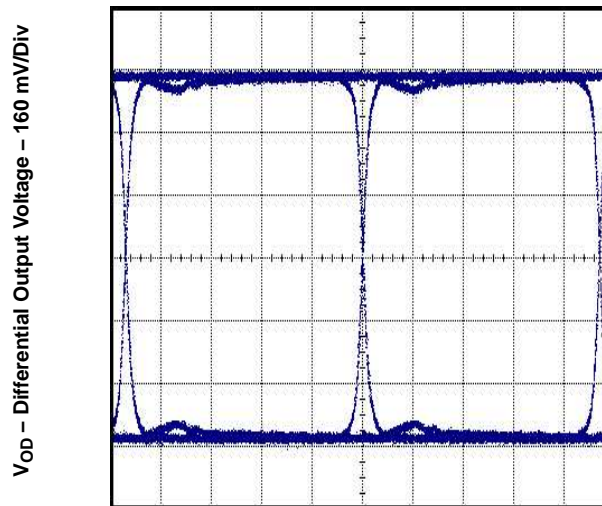
t – Time – 200 ps/Div

G012

Figure 18.

APPLICATION INFORMATION

Figure 19 shows a typical application circuit using the ONET4291PA with a microprocessor for digital control of the LOS threshold, output amplitude, and bandwidth.
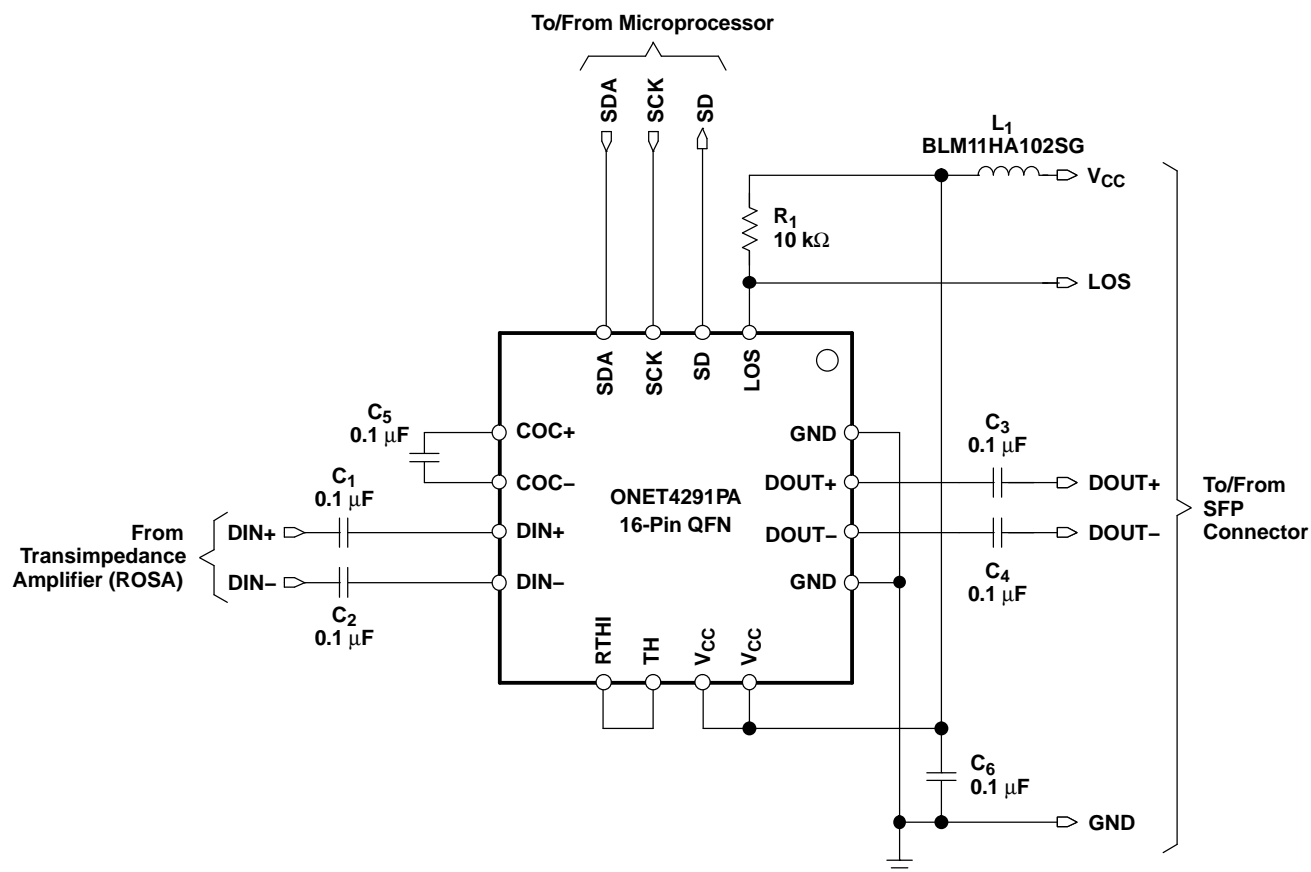
S0099-01

Figure 19. Basic Application Circuit With Digital Control

APPLICATION INFORMATION (continued)

Figure 20 shows a typical application without digital control. In this case, the output amplitude and bandwidth are fixed. The LOS threshold is adjusted by means of a resistor connected to the TH terminal.

S0099-02

Figure 20. Basic Application Circuit With External LOS Threshold Resistor

PACKAGING INFORMATION

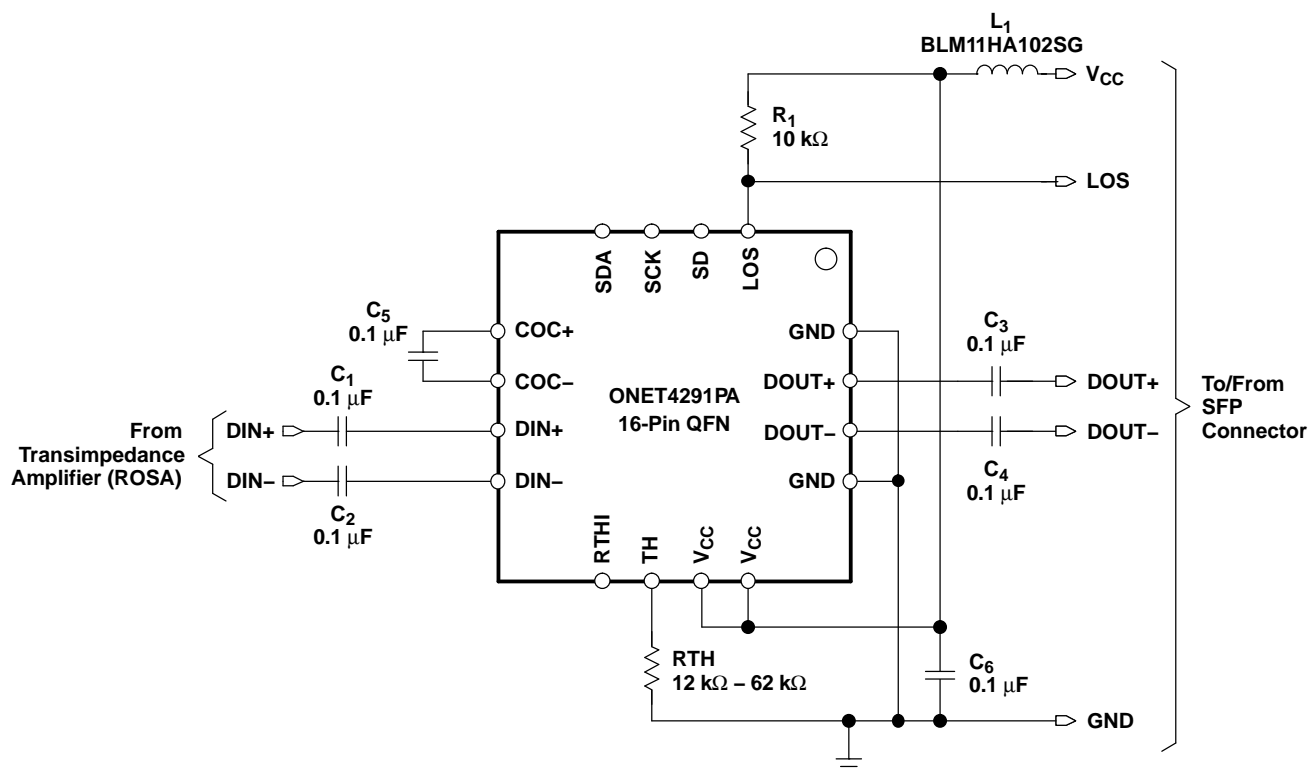| Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
ONET4291PARGVR	ACTIVE	VQFN	RGV	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	4291PA	Samples
ONET4291PARGVRG4	ACTIVE	VQFN	RGV	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	4291PA	Samples
ONET4291PARGVT	ACTIVE	VQFN	RGV	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	4291PA	Samples
ONET4291PARGVTG4	ACTIVE	VQFN	RGV	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	4291PA	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Only one of markings shown within the brackets will appear on the physical device.

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PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ONET4291PARGVR	VQFN	RGV	16	2500	330.0	12.4	4.3	4.3	1.5	8.0	12.0	Q2
ONET4291PARGVT	VQFN	RGV	16	250	330.0	12.4	4.3	4.3	1.5	8.0	12.0	Q2

PACKAGE MATERIALS INFORMATION

TAPE AND REEL BOX DIMENSIONS

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ONET4291PARGVR	VQFN	RGV	16	2500	338.1	338.1	20.6
ONET4291PARGVT	VQFN	RGV	16	250	338.1	338.1	20.6

RGV (S-PVQFN-N16)   PLASTIC QUAD FLATPACK NO-LEAD

$\dfrac{4,15}{3,85}$ A

B

$\dfrac{4,15}{3,85}$

PIN 1 INDEX AREA
TOP AND BOTTOM

$\dfrac{1,00}{0,80}$

0,20 REF.

SEATING PLANE

⌒ 0,08

$\dfrac{0,05}{0,00}$ C

$16\times \dfrac{0,65}{0,45}$

0,65

1   4

16   5

THERMAL PAD

SIZE AND SHAPE
SHOWN ON SEPARATE SHEET

13   8

12   9

$16\times \dfrac{0,38}{0,23}$

⊕ | 0,10 Ⓜ C A B
  | 0,05 Ⓜ C

4203497/F 06/11
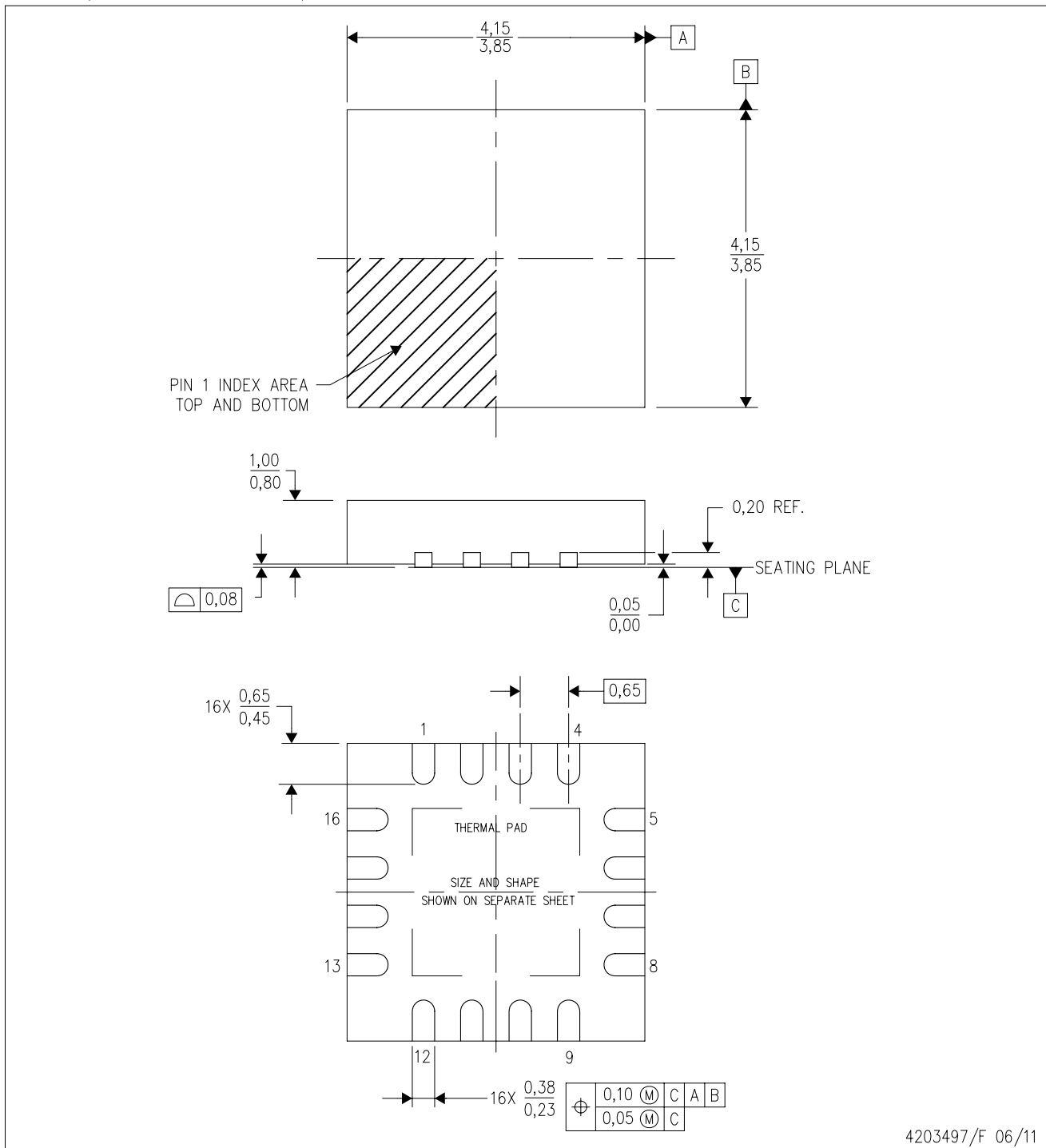
NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
          B. This drawing is subject to change without notice.
          C. Quad Flatpack, No-leads (QFN) package configuration.
          D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
          E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
          F. Falls within JEDEC MO-220.

TEXAS INSTRUMENTS
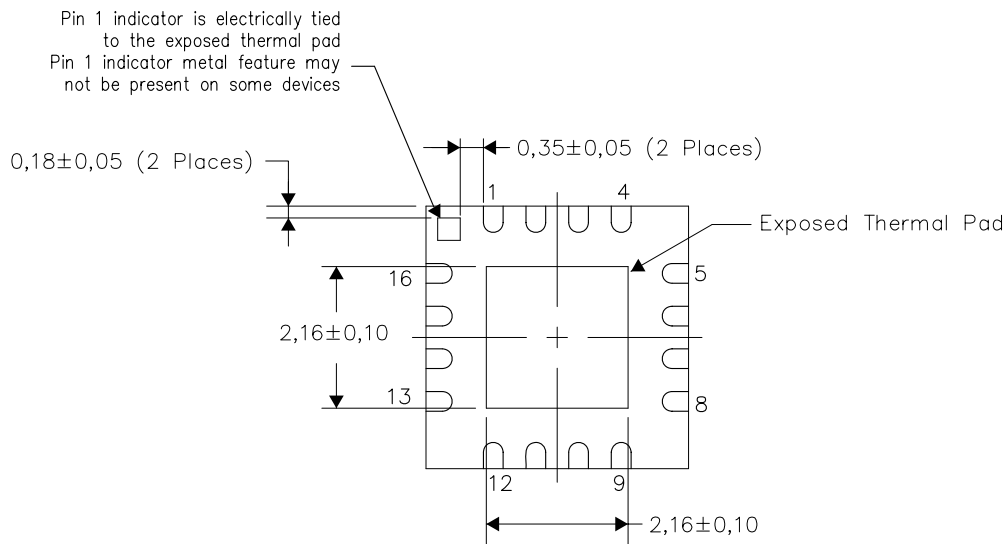www.ti.com

RGV (S−PVQFN−N16)   PLASTIC QUAD FLATPACK NO−LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No−Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

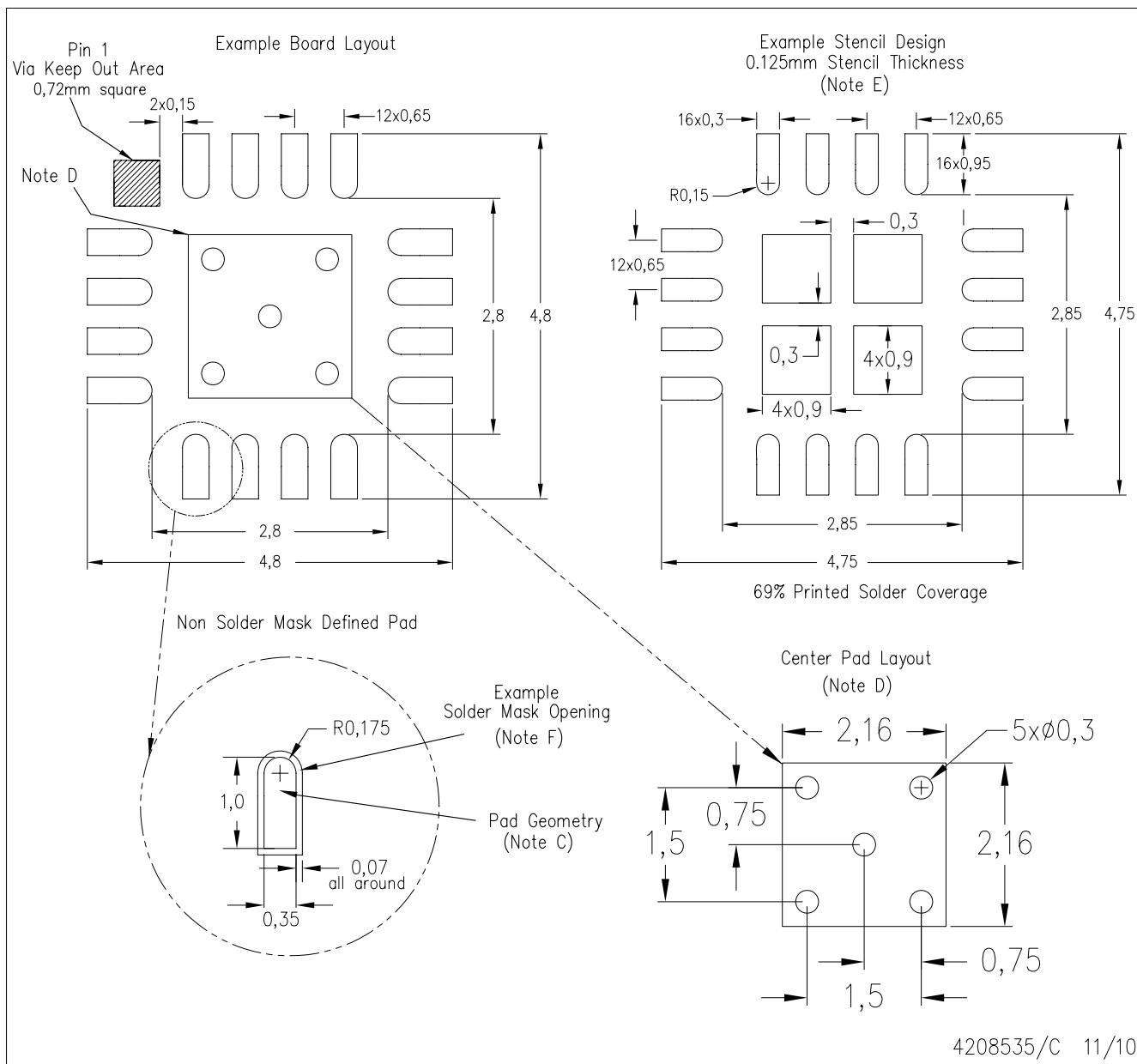The exposed thermal pad dimensions for this package are shown in the following illustration.

Pin 1 indicator is electrically tied
to the exposed thermal pad
Pin 1 indicator metal feature may
not be present on some devices

0,18±0,05 (2 Places)

0,35±0,05 (2 Places)

Exposed Thermal Pad

2,16±0,10

2,16±0,10

Bottom View

Exposed Thermal Pad Dimensions

4206351−2/J 06/11

NOTE: All linear dimensions are in millimeters

RGV (S−PVQFN−N16)   PLASTIC QUAD FLATPACK NO−LEAD

Example Board Layout

Pin 1
Via Keep Out Area
0,72mm square

2x0,15

12x0,65

Note D

2,8   4,8

2,8

4,8

Non Solder Mask Defined Pad

Example
Solder Mask Opening
(Note F)

R0,175

1,0

Pad Geometry
(Note C)

0,07
all around

0,35

Example Stencil Design
0.125mm Stencil Thickness
(Note E)

16x0,3

12x0,65

16x0,95

R0,15

0,3

12x0,65

2,85   4,75

0,3

4x0,9

4x0,9

2,85

4,75

69% Printed Solder Coverage

Center Pad Layout
(Note D)

2,16

5x∅0,3

0,75

1,5

2,16

0,75

1,5

4208535/C 11/10

NOTES: A. All linear dimensions are in millimeters.
        B. This drawing is subject to change without notice.
        C. Publication IPC−7351 is recommended for alternate designs.
        D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN
            Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets
            for specific thermal information, via requirements, and recommended board layout. These documents are available at
            www.ti.com <http://www.ti.com>.
        E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should
            contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
        F. Customers should contact their board fabrication site for solder mask tolerances.

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